THERMAL DATA

R _{thj-case} Thermal Resistance Junction-Case	Max	0.63	°C/W
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ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

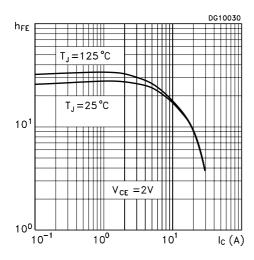
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CER}	Collector Cut-off Current (R_{BE} = 5 Ω)	$V_{CE} = 1000 V$ $V_{CE} = 1000 V$ $T_{C} = 100 {}^{o}C$			0.2 1	mA mA
ICEV	Collector Cut-off Current (V _{BE} = -1.5V)	$V_{CE} = 1000 V$ $V_{CE} = 1000 V$ $T_{C} = 100 °C$			0.2 1	mA mA
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 5 V			1	mA
V _{CEO(sus)} *	Collector-Emitter Sustaining Voltage (I _B = 0)	I _C = 200 mA L = 25 mH	450			V
V _{EBO}	Emitter Base Voltage (I _C = 0)	I _E = 50 mA	7			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	$ \begin{array}{ll} I_{C} = 10A & I_{B} = 1 \ A \\ I_{C} = 10 \ A & I_{B} = 1 \ A \ T_{C} = 100^{\circ}C \\ I_{C} = 20 \ A & I_{B} = 4 \ A \\ I_{C} = 20 \ A & I_{B} = 4 \ A \ T_{C} = 100^{\circ}C \end{array} $		0.8 0.5	2.8 2	> > > >
V _{BE(sat)} *	Base-Emitter Saturation Voltage			0.9 1.1	1.5 1.5	V V V V
di _c /dt	Rate of rise on-state Collector Current	$ \begin{array}{lll} V_{CC} = 300 \; V & R_C = 0 & t_p = 3 \; \mu s \\ I_{B1} = 1.5 \; A & T_C = 25^\circ C \\ I_{B1} = 1.5 \; A & T_C = 100^\circ C \\ I_{B1} = 6 \; A & T_C = 100^\circ C \end{array} $	70 150	100		A/μs A/μs A/μs
V _{CE} (3μs)	Collector-Emitter Dynamic Voltage			2.1	8	>
V _{CE} (5µs)	Collector-Emitter Dynamic Voltage			1.1	4	>
t _s t _f t _c	INDUCTIVE LOAD Storage Time Fall Time Cross Over Time			1 0.05 0.08		μs μs μs
t _s t _f t _c	INDUCTIVE LOAD Storage Time Fall Time Cross Over Time	$ \begin{array}{ll} I_{C} = 10 \mbox{ A} & V_{CC} = 50 \mbox{ V} \\ V_{BB} = -5 \mbox{ V} & R_{BB} = 0.6 \Omega \\ V_{clamp} = 400 \mbox{ V} & I_{B1} = 1 \mbox{ A} \\ L = 0.25 \mbox{ mH} & T_{C} = 100^{\circ} \mbox{C} \end{array} $			2 0.1 0.18	μs μs μs
V _{CEW}	Maximum Collector Emitter Voltage without Snubber		500			V
t _s t _f t _c	INDUCTIVE LOAD Storage Time Fall Time Cross Over Time	$ \begin{array}{ll} I_{C} = 10 \; A & & V_{CC} = 50 \; V \\ V_{BB} = 0 & & R_{BB} = 0.15 \; \Omega \\ V_{clamp} = 400 \; V & & I_{B1} = 1 \; A \\ L = 0.25 \; mH \end{array} $		1.5 0.04 0.07		μs μs μs

Symbol	Parameter	Test Con	Test Conditions		Тур.	Max.	Unit
t _s t _f t _c	INDUCTIVE LOAD Storage Time Fall Time Cross Over Time	$I_{C} = 10 \text{ A}$ $V_{BB} = 0$ $V_{clamp} = 400 \text{ V}$ L = 0.25 mH	$V_{CC} = 50 V R_{BB} = 0.15 \Omega I_{B1} = 1 A T_{C} = 100^{\circ}C$			3 0.15 0.25	μs μs μs
V _{CEW}	Maximum Collector Emitter Voltage without Snubber	$I_{C} = 10 A$ $V_{BB} = 0$ $I_{B1} = 1 A$ $T_{C} = 125^{\circ}C$	V_{CC} = 50 V R _{BB} = 0.15 Ω L = 0.25 mH	500			V
t _s t _f t _c	INDUCTIVE LOAD Storage Time Fall Time Cross Over Time	$I_{C} = 20 \text{ A}$ $V_{BB} = -5 \text{ V}$ $V_{clamp} = 400 \text{ V}$ L = 0.12 mH	V _{CC} = 50 V R _{BB} =0.6 Ω I _{B1} = 4 A		2.2 0.06 0.12		μs μs μs
t _s t _f t _c	INDUCTIVE LOAD Storage Time Fall Time Cross Over Time	$I_{C} = 20 \text{ A}$ $V_{BB} = -5 \text{ V}$ $V_{clamp} = 400 \text{ V}$ L = 0.12 mH	$V_{CC} = 50 V$ $R_{BB} = 0.6 \Omega$ $I_{B1} = 4 A$ $T_{C} = 125^{\circ}C$			3.5 0.12 0.3	μs μs μs
V _{CEW}	Maximum Collector Emitter Voltage without Snubber	$I_{CWoff} = 30 \text{ A}$ $V_{BB} = -5 \text{ V}$ L = 0.12 mH $T_{C} = 125^{\circ}\text{C}$	V _{CC} = 50 V R _{BB} = 0.6 Ω I _{B1} = 6 A	400			V

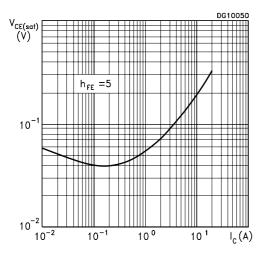
ELECTRICAL CHARACTERISTICS (continued)

A7/

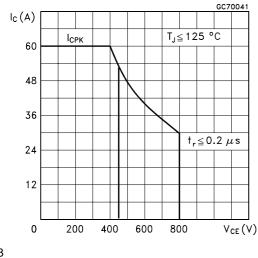
DC Current Gain



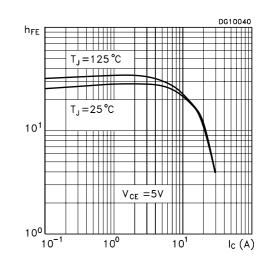
Collector Emitter Saturation Voltage



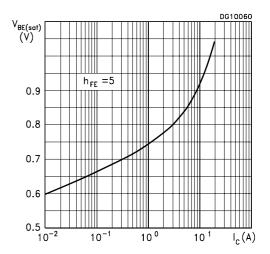
Forward Biased Safe Operating Area



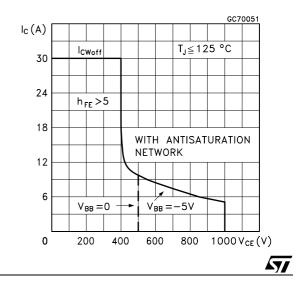
DC Current Gain











Storage Time Versus Pulse Time.

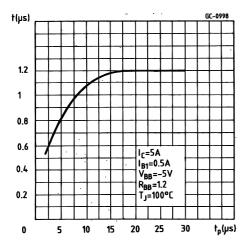
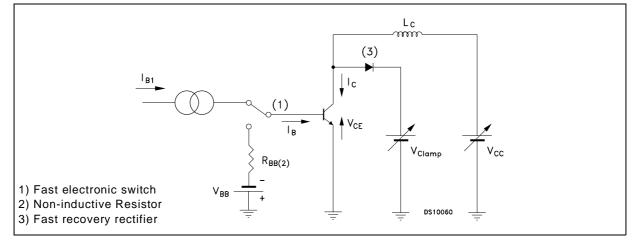
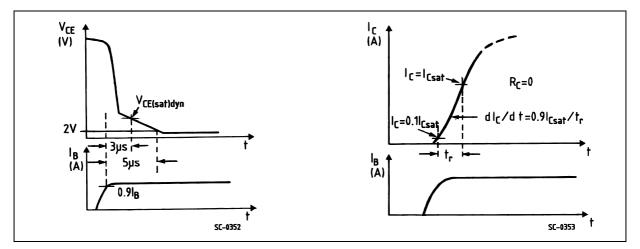


Figure 1: Inductive Load Switching Test Circuit.

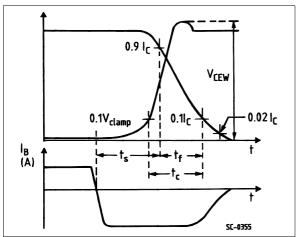


BUF420AW

Turn-on Switching Test Waveforms.

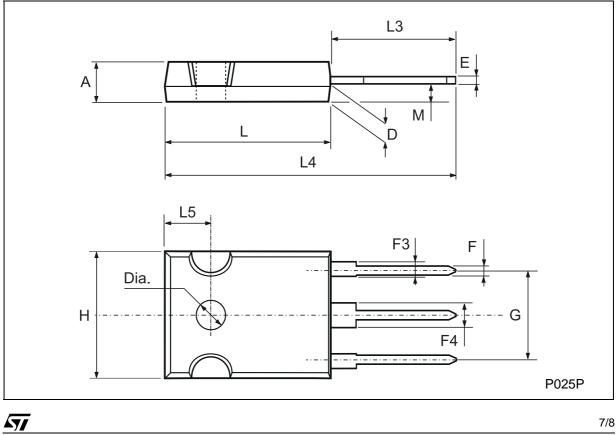


Turn-off Switching Test Waveforms (inductive load).



DIM.	mm			inch			
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	4.7		5.3	0.185		0.209	
D	2.2		2.6	0.087		0.102	
Е	0.4		0.8	0.016		0.031	
F	1		1.4	0.039		0.055	
F3	2		2.4	0.079		0.094	
F4	3		3.4	0.118		0.134	
G		10.9			0.429		
Н	15.3		15.9	0.602		0.626	
L	19.7		20.3	0.776		0.779	
L3	14.2		14.8	0.559		0.582	
L4		34.6			1.362		
L5		5.5			0.217		
М	2		3	0.079		0.118	





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